**Amendments to the Abstract:**

Please replace the Abstract with the following rewritten Abstract:

--The present ~~invention~~ disclosure relates to a method for fabricating an image sensor capable of improving [[a]] dark current characteristics. The method includes: ~~the steps of:~~ forming sequentially a pad oxide layer and a pad nitride layer on a substrate and selectively removing a portion of the pad oxide layer and a first portion of the pad nitride layer to expose a surface of the substrate [[in]] on which a field insulation layer will be formed; forming ~~the field insulation layer~~ a first ion-implantation region by performing a first ~~channel stop~~ ion-implantation process [[to]] on the exposed surface of the substrate ~~with use of~~ using the remaining pad nitride layer that exists after removal of the first portion of the pad nitride layer as a first mask; performing a thermal oxidation process to form the field insulation layer on the exposed surface of the substrate; removing a ~~partial~~ second portion of the pad nitride layer so that [[one]] a side of the remaining pad nitride layer that exists after removal of the second portion of the pad nitride layer is spaced ~~out with a predetermined distance from an edge of the field insulation layer;~~ apart from an edge of the field insulation layer by a distance; and forming a second ion-implantation region by performing ~~an additional~~ a second ion-implantation process ~~onto~~ on ~~the exposed substrate surface and~~ the field insulation layer [[by]] using the remaining pad nitride layer that exists after removal of the second portion of the pad nitride layer as a second mask.--